

# PMBT4401YS

# 40 V, 600 mA, double NPN switching transistor

**Product data sheet** 

### 1. General description

Double NPN switching transistor in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package.

Double PNP complement: PMBT4403YS

### 2. Features and benefits

- Double general-purpose switching transistor
- High current (max. 600 mA)
- Voltage max. 40 V
- AEC-Q101 qualified

# 3. Applications

Switching and linear amplification

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions   | Min | Тур | Max | Unit |
|------------------|---------------------------|--|-----|-----|-----|------|
| Per transist     | tor                       |  |     |     |     | ,    |
| V <sub>CEO</sub> | collector-emitter voltage | open base  | -   | -   | 40  | V    |
| I <sub>C</sub>   | collector current         |  | -   | -   | 600 | mA   |
| Per transist     | tor                       |  |     |     |     |      |
| h <sub>FE</sub>  | DC current gain           | $V_{CE}$ = 1 V; $I_{C}$ = 150 mA; $t_{p}$ ≤ 300 μs; $δ$ ≤ 0.02; $T_{amb}$ = 25 °C      | 100 | -   | 300 |      |
|                  |                           | $V_{CE}$ = 2 V; $I_{C}$ = 500 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C | 40  | -   | -   |      |



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# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description   | Simplified outline | Graphic symbol |
|-----|--------|---------------|--------------------|----------------|
| 1   | E      | emitter TR1   | <u>654</u>         | 6 5 4          |
| 2   | В      | base TR1      |                    | P = 100        |
| 3   | С      | collector TR2 | 0                  | TR1 TR2        |
| 4   | E      | emitter TR2   | ☐1 ☐2 ☐3           |                |
| 5   | В      | base TR2      | TSSOP6 (SOT363)    | 1 2 3          |
| 6   | С      | collector TR1 |                    | sym020         |

# 6. Ordering information

Table 3. Ordering information

| Type number |            | Package |  |         |  |
|-------------|------------|---------|--|---------|--|
|             |            | Name    | Description                              | Version |  |
|             | PMBT4401YS | TSSOP6  | plastic surface-mounted package; 6 leads | SOT363  |  |

# 7. Marking

Table 4. Marking codes

| Type number | Marking code [1] |
|-------------|------------------|
| PMBT4401YS  | BG%              |

[1] % = placeholder for manufacturing site code

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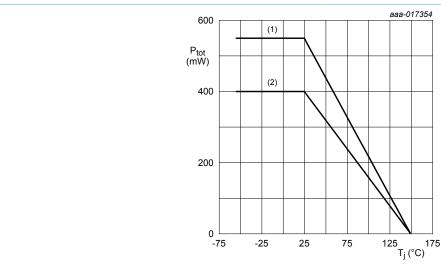
### 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|-----|------|
| Per transist     | tor                       | '                                   |     |     |     |      |
| $V_{CBO}$        | collector-base voltage    | open emitter                        |     | -   | 60  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | 40  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | 6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | 600 | mA   |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | 800 | mA   |
| I <sub>BM</sub>  | peak base current         |                                     |     | -   | 200 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 250 | mW   |
|                  |                           |                                     | [2] | -   | 300 | mW   |
| Per device       |                           |                                     |     |     |     | ,    |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 400 | mW   |
|                  |                           |                                     | [2] | -   | 550 | mW   |
| T <sub>j</sub>   | junction temperature      |                                     |     | -   | 150 | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150 | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150 | °C   |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint
- Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm<sup>2</sup>.



- (1) FR4 PCB; mounting pad for collector 1 cm<sup>2</sup>
- (2) FR4 PCB; standard footprint

Fig. 1. Per device: Power derating curves SOT363 (SC-88)

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### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol               | Parameter                | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|--------------------------|-------------|-----|-----|-----|-----|------|
| Per transist         | tor                      |             |     |     |     |     |      |
| R <sub>th(j-a)</sub> | thermal resistance       | in free air | [1] | -   | -   | 500 | K/W  |
|                      | from junction to ambient |             | [2] | -   | -   | 417 | K/W  |
| Per device           |                          |             |     |     | '   |     |      |
| R <sub>th(j-a)</sub> | thermal resistance       | in free air | [1] | -   | -   | 313 | K/W  |
|                      | from junction to ambient |             | [2] | -   | -   | 227 | K/W  |

- [1] Device mounted on an FR4 PCB; single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 1 cm<sup>2</sup>.

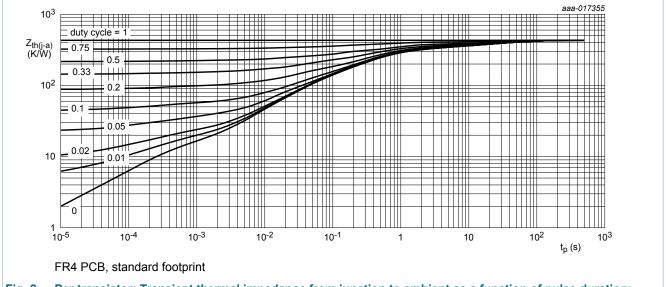


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

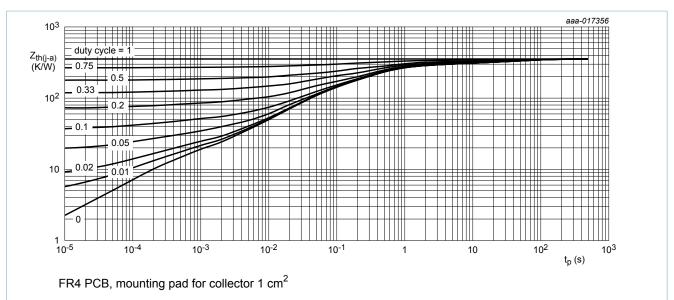


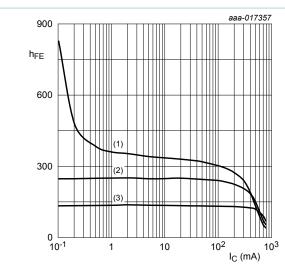
Fig. 3. Per Transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

Table 7. Characteristics

| Symbol             | Parameter                            | Conditions   | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|--|-----|-----|-----|------|
| Per transi         | stor                                 |  |     |     |     |      |
| I <sub>CBO</sub>   | collector-base cut-off               | $V_{CB}$ = 50 V; $I_{E}$ = 0 A; $T_{amb}$ = 25 °C  | -   | -   | 50  | nA   |
|                    | current                              | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 125 ^{\circ}\text{C}$                                 | -   | -   | 10  | μA   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | $V_{EB} = 6 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$                             | -   | -   | 50  | nA   |
| h <sub>FE</sub>    | DC current gain                      | $V_{CE}$ = 1 V; $I_{C}$ = 0.1 mA; $T_{amb}$ = 25 °C  | 20  | -   | -   |      |
|                    |                                      | $V_{CE}$ = 1 V; $I_{C}$ = 1 mA; $T_{amb}$ = 25 °C  | 40  | -   | -   |      |
|                    |                                      | $V_{CE}$ = 1 V; $I_{C}$ = 10 mA; $T_{amb}$ = 25 °C   | 80  | -   | -   |      |
|                    |                                      | $V_{CE}$ = 1 V; $I_{C}$ = 150 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                 | 100 | -   | 300 |      |
|                    |                                      | $V_{CE}$ = 2 V; $I_{C}$ = 500 mA; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                 | 40  | -   | -   |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | $I_C$ = 150 mA; $I_B$ = 15 mA; $t_p \le 300 \ \mu s$ ;<br>δ ≤ 0.02; $T_{amb}$ = 25 °C                  | -   | -   | 400 | mV   |
|                    |                                      | $I_{C}$ = 500 mA; $I_{B}$ = 50 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                | -   | -   | 750 | mV   |
| V <sub>BEsat</sub> | base-emitter saturation voltage      | $I_C$ = 150 mA; $I_B$ = 15 mA; $t_p \le$ 300 μs; $δ \le$ 0.02; $T_{amb}$ = 25 °C                       | -   | -   | 950 | mV   |
|                    |                                      | $I_{C}$ = 500 mA; $I_{B}$ = 50 mA; $t_{p}$ ≤ 300 µs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C                | -   | -   | 1.2 | V    |
| t <sub>d</sub>     | delay time                           | I <sub>C</sub> = 150 mA; I <sub>Bon</sub> = 15 mA;   | -   | -   | 10  | ns   |
| t <sub>r</sub>     | rise time                            | I <sub>Boff</sub> = -15 mA; T <sub>amb</sub> = 25 °C   | -   | -   | 25  | ns   |
| t <sub>on</sub>    | turn-on time                         |  | -   | -   | 35  | ns   |
| t <sub>s</sub>     | storage time                         |  | -   | -   | 200 | ns   |
| t <sub>f</sub>     | fall time                            |  | -   | -   | 60  | ns   |
| t <sub>off</sub>   | turn-off time                        |  | -   | -   | 250 | ns   |
| C <sub>C</sub>     | collector capacitance                | $V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$<br>f = 1 MHz; $T_{amb} = 25 \text{ °C}$ | -   | -   | 8   | pF   |
| C <sub>E</sub>     | emitter capacitance                  | $V_{EB}$ = 500 mV; $I_{C}$ = 0 A; f = 1 MHz;<br>$T_{amb}$ = 25 °C                                      | -   | -   | 30  | pF   |
| f <sub>T</sub>     | transition frequency                 | $V_{CE}$ = 20 V; $I_{C}$ = 20 mA; f = 100 MHz;<br>$T_{amb}$ = 25 °C                                    | 250 | -   | -   | MHz  |
| NF                 | noise figure                         | $V_{CE} = 5 \text{ V}; I_{C} = 100  \mu\text{A}; R_{S} = 1  k\Omega;$ f = 1 kHz                        | -   | -   | 4   | dB   |



(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values

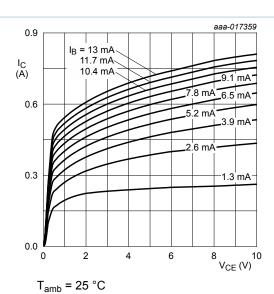
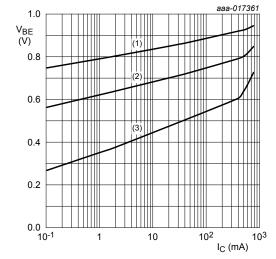


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



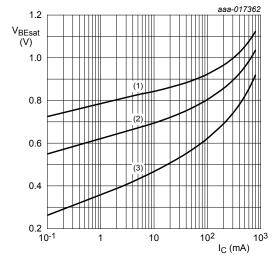
$$V_{CE} = 10 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



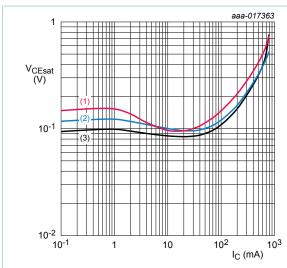
$$I_{\rm C}/I_{\rm B} = 10$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



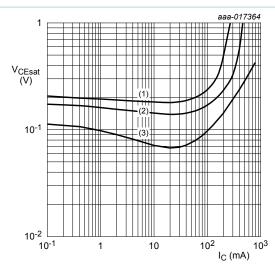
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

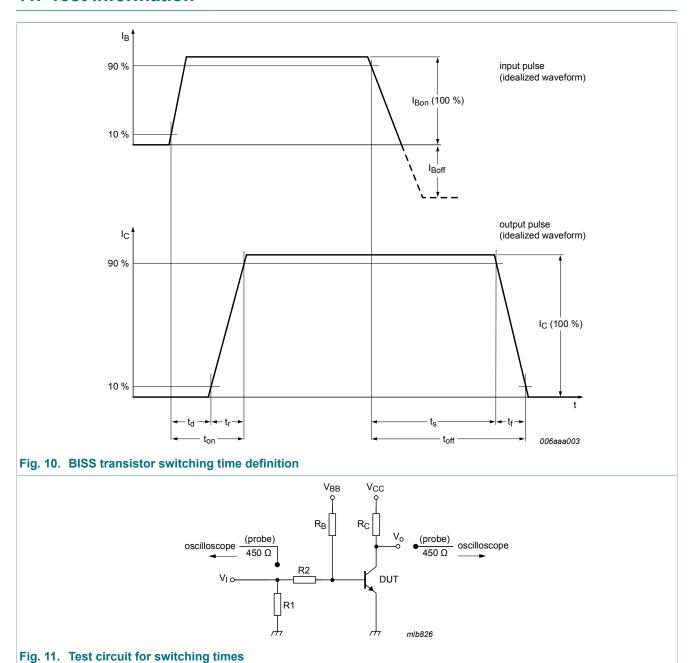
(2) 
$$I_{\rm C}/I_{\rm B} = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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### 11. Test information

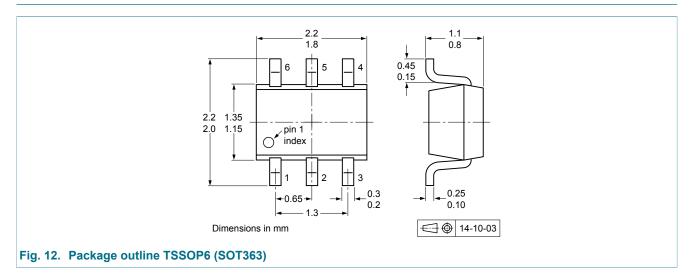


### 11.1 Quality information

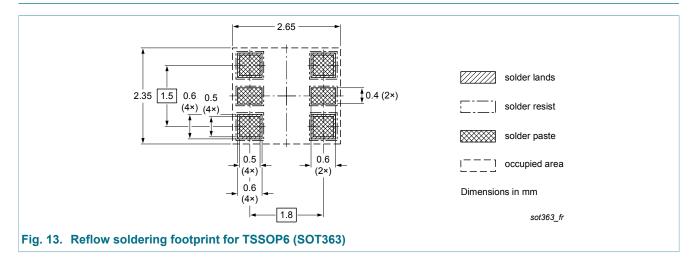
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

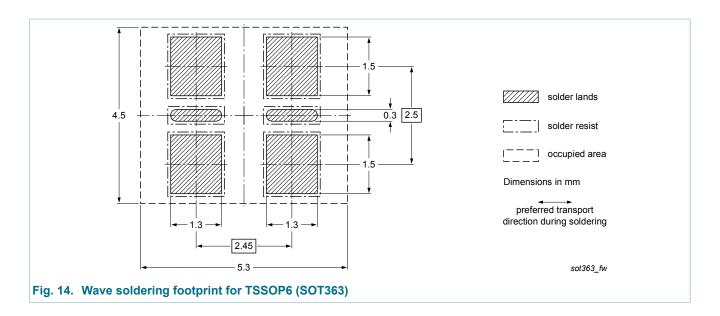
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### 12. Package outline



# 13. Soldering





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# 14. Revision history

### Table 8. Revision history

| Data sheet ID  | Release date | Data sheet status  | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PMBT4401YS v.1 | 20150702     | Product data sheet | -             | -          |

#### 40 V, 600 mA, double NPN switching transistor

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#### 15.1 Data sheet status

| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary<br>[short] data<br>sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product<br>[short] data<br>sheet     | Production         | This document contains the product specification.                                     |

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